

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)	PATENT APPLICATION
)	
Inventors: Jong-Jan Lee and Sheng Teng)	
Hsu)	
)	
Serial No.: Not Yet Assigned)	Attorney Docket No.
)	SLA 0696
Filed: Herewith)	
)	
Title: FABRICATION OF SILICON-ON-))	
NOTHING (SON) MOSFET)	
FABRICATION USING)	
SELECTIVE ETCHING)	
Si _{1-x} Ge _x LAYER)	
)	

Honorable Commissioner for Patents
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

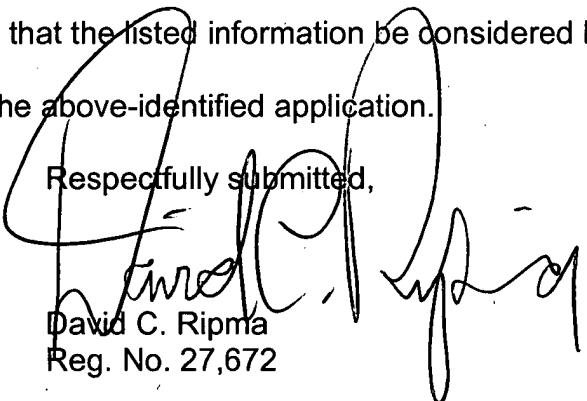
Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by
the Examiner and made of record in the above-identified application.

(Date) 7/22/03

Respectfully submitted,


David C. Ripma
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1449A/PTO Rev. 10/95 LIST OF PRIOR ART CITED BY APPLICANT <i>(use as many sheets as necessary)</i>		Complete If Known			
		Application Number			
		Filing Date		07-22-03	
		First Named Inventor		Jong-Jan Lee	
		Group Art Unit			
		Examiner Name			
Sheet	1	of	1	Attorney Docket No.	SLA.0696

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No. ¹	U.S. Patent Document Kind Number Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear	

FOREIGN PATENT DOCUMENTS							
Examiner Initials	Cite No. ¹	Foreign Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear	T ⁶
		Office ³	Number ⁴				

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS							
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source.					T ²
		M. JURCZAK ET AL., SON (<i>Silicon on Nothing</i>) - A New Device Architecture for the ULSI Era, VLSI Tech. Dig., p.29, (1999).					
		R. KOH, Buried Layer Engineering to Reduce the Drain-Induced Barrier Lowering of Sub-0.05um SOI-MOSFET Jpn. J. Appl. Phys., Vol. 38, P. 2294 (1999)					
		M. JURCZAK, ET AL., Silicon-on-Nothing (SON) - an innovative Process for Advanced CMOS, IEEE Trans. El. Dev. Vol. 47, pp2179-2187 (2000).					
		R. CHAU ET AL., A 50nm Depleted-Substrate CMOS Transistor, IEDM, p. 621, 2001.					
		T. SATO ET AL., SON (<i>Silicon on Nothing</i>) MOSFET Using ESS (Empty Space in Silicon) Technique for SoC Application, IEDM, p. 809, 2001.					

Examiner Signature		Date Considered	
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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.1⁶ if possible. ⁶Applicant is to place a check mark here if English language Translation is attached